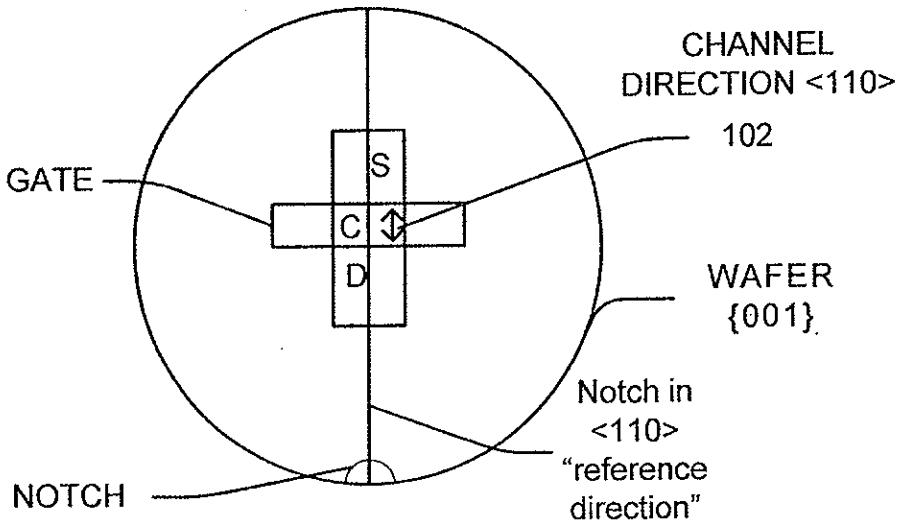


FIGURE 1A
PRIOR ART

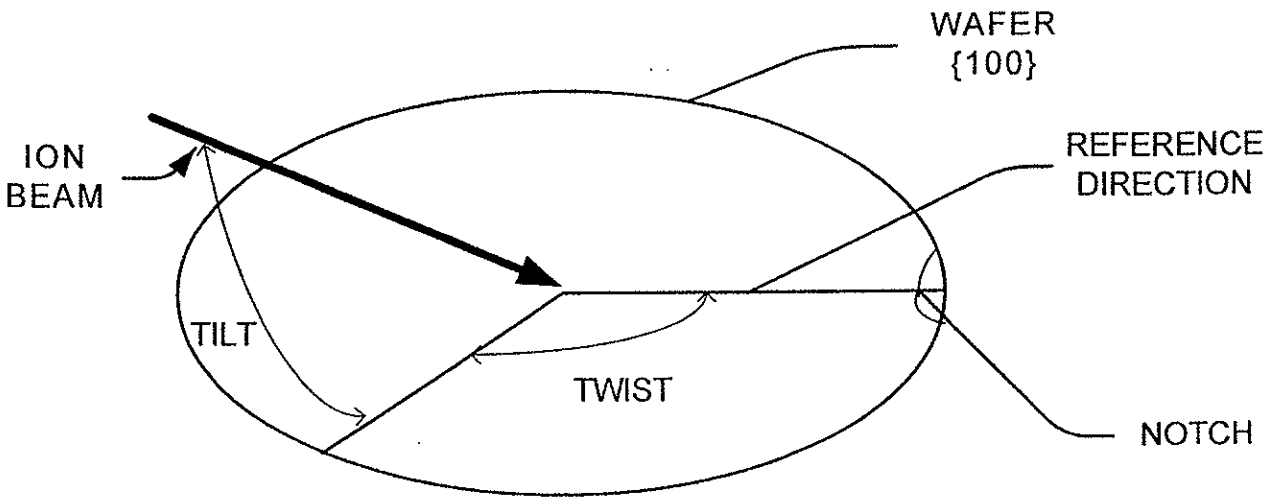


FIGURE 1B
PRIOR ART

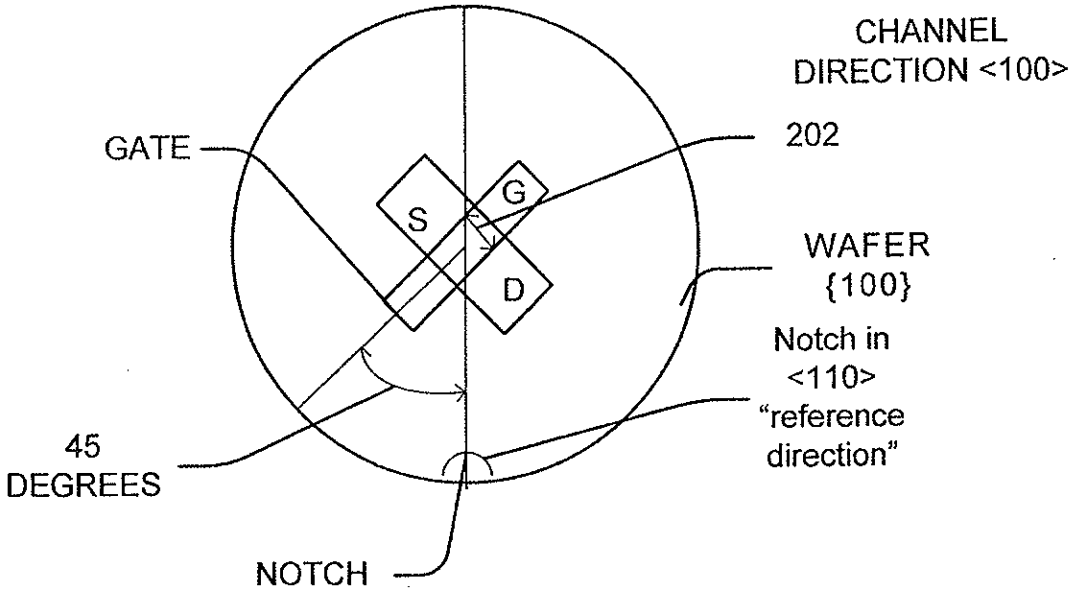


FIGURE 2A

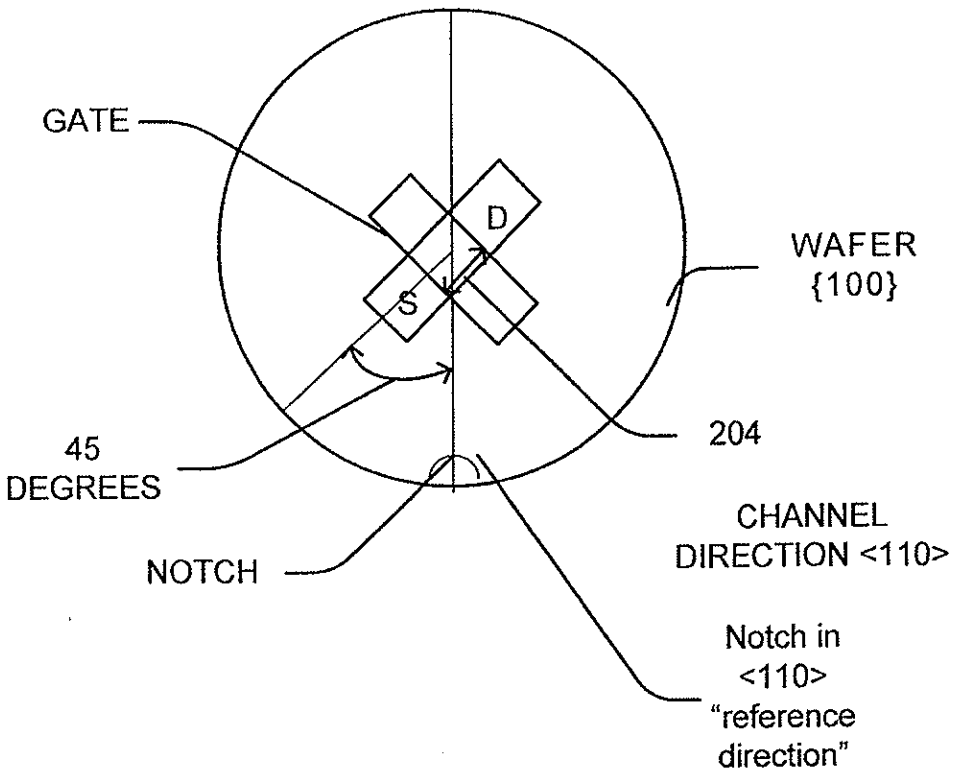


FIGURE 2B

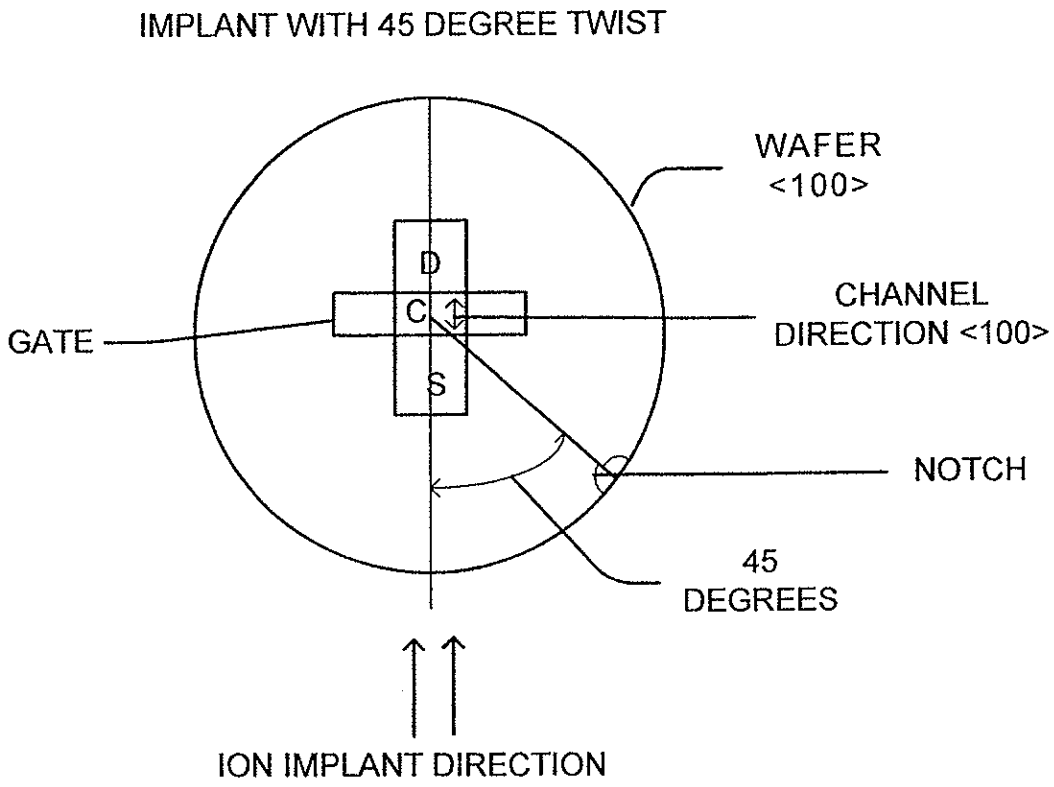


FIGURE 3A

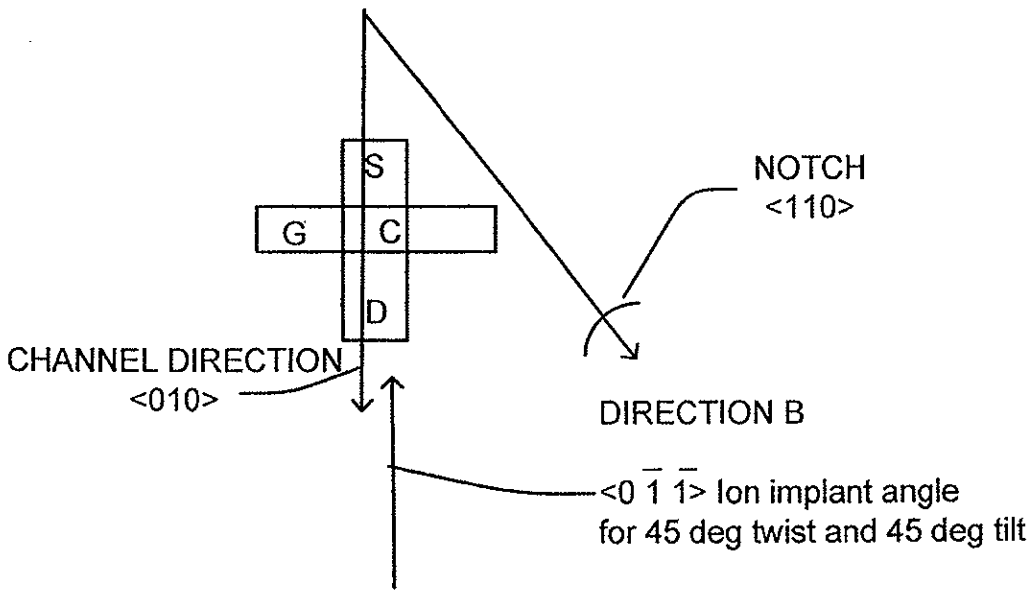


FIGURE 3B

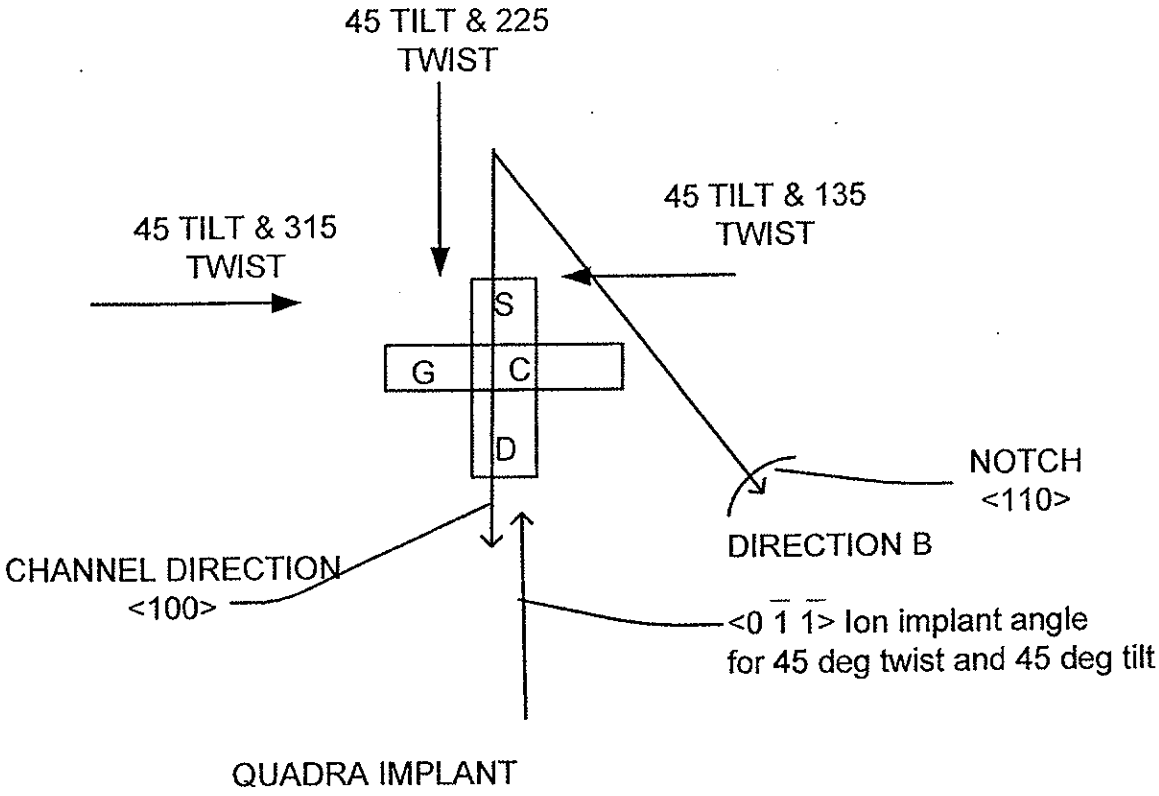

45 TILT & 225
TWIST
45 TILT & 315
TWIST
45 TILT & 135
TWIST
S
G
C
D
NOTCH
<110>
DIRECTION B
CHANNEL DIRECTION
<100>
<0 $\bar{1}$ $\bar{1}$> Ion implant angle
for 45 deg twist and 45 deg tilt
QUADRA IMPLANT

FIGURE 3C

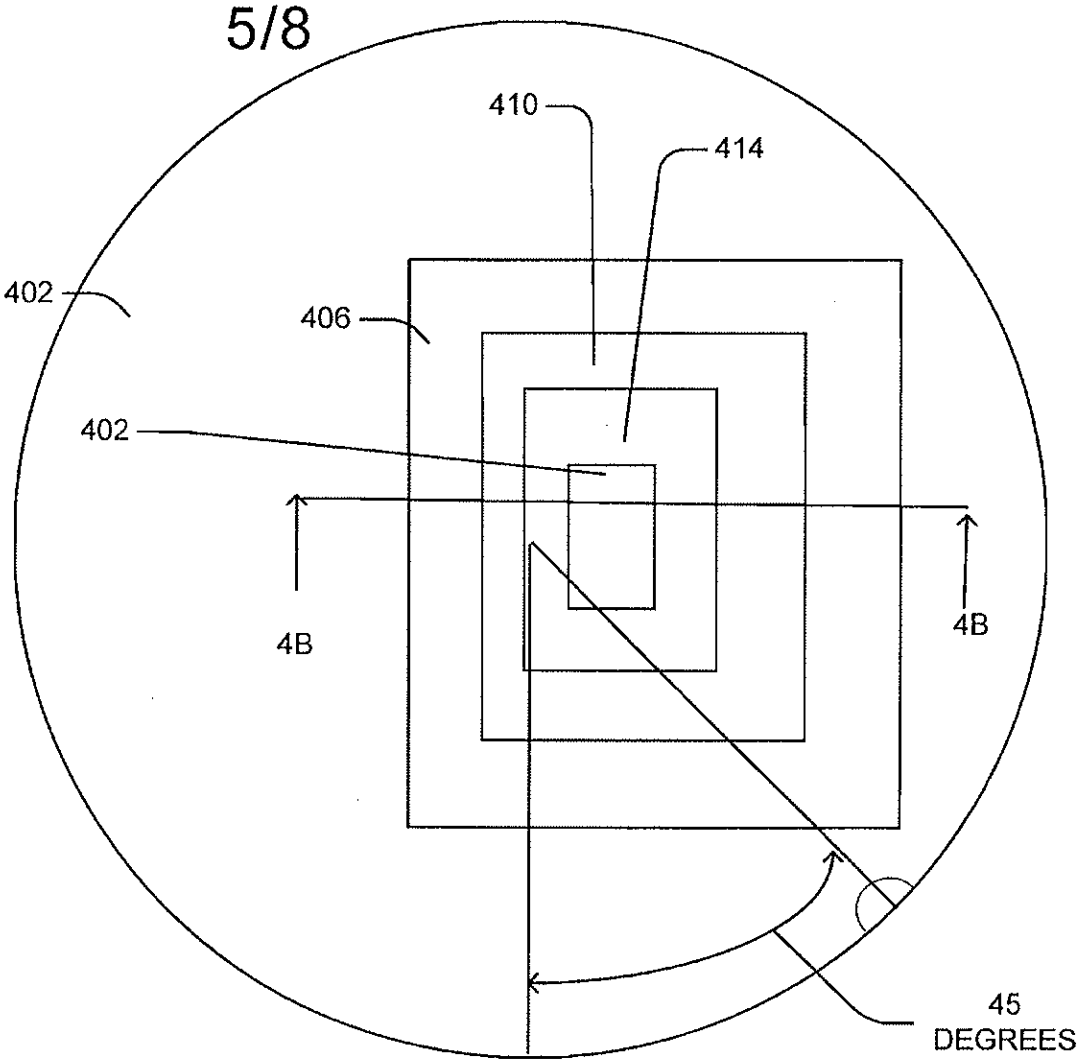


FIGURE 4A

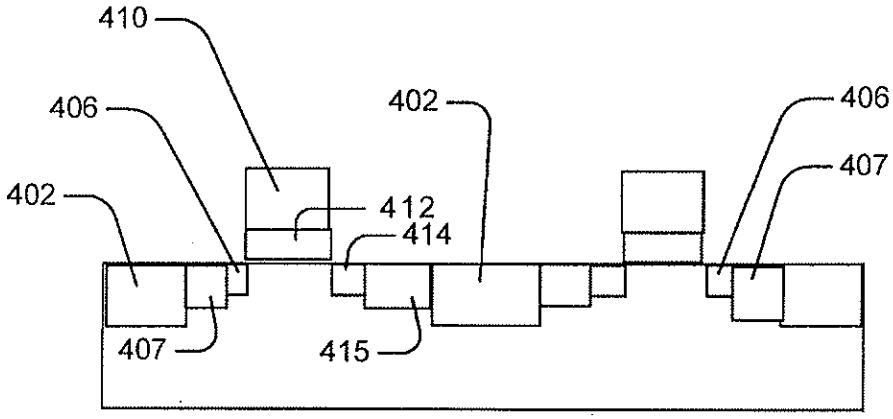


FIGURE 4B

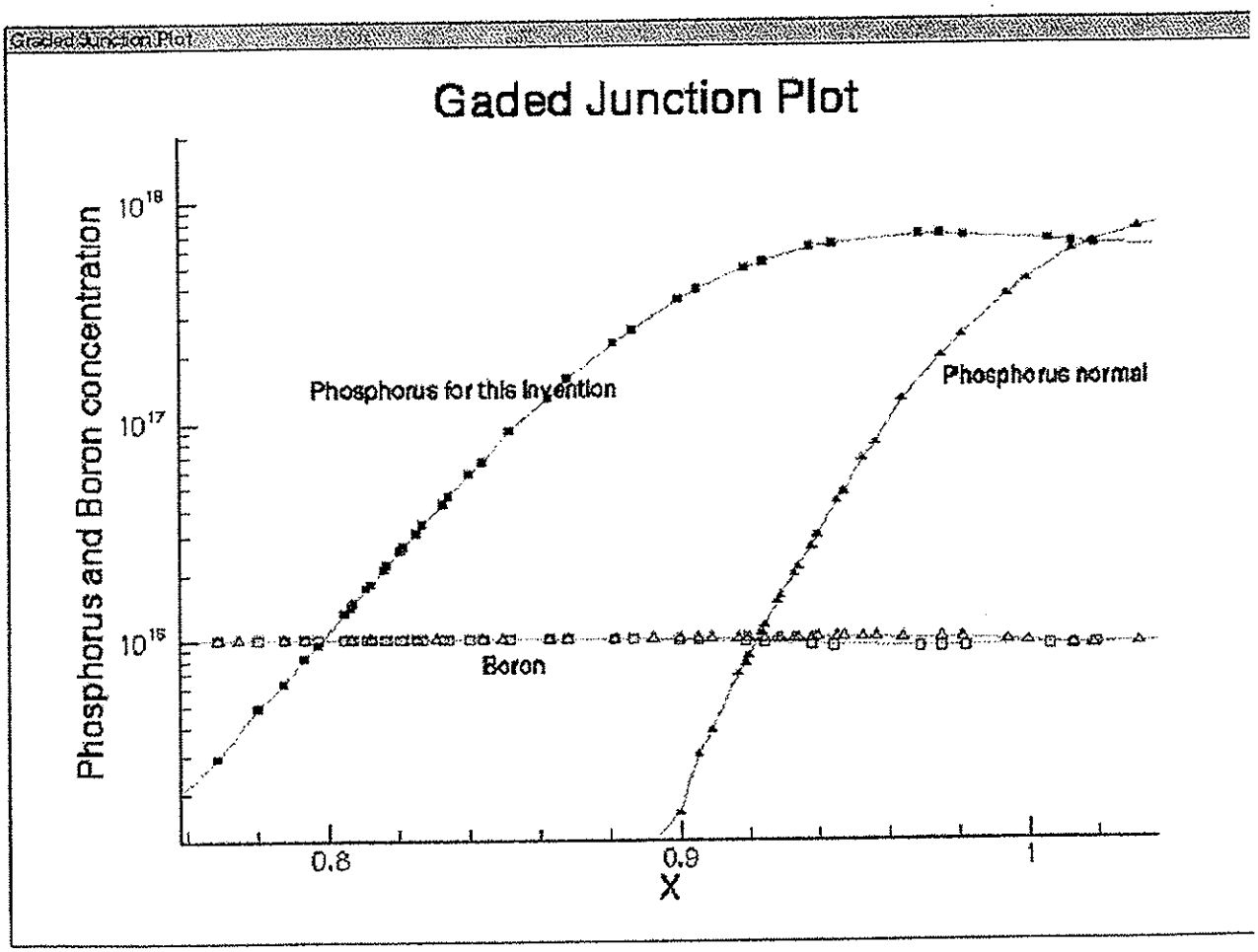

Graded Junction Plot
Gaded Junction Plot
Phosphorus and Boron concentration
10^{18}
10^{17}
10^{15}
Phosphorus for this invention
Phosphorus normal
Boron
0.8
0.9
1
X

FIGURE 5

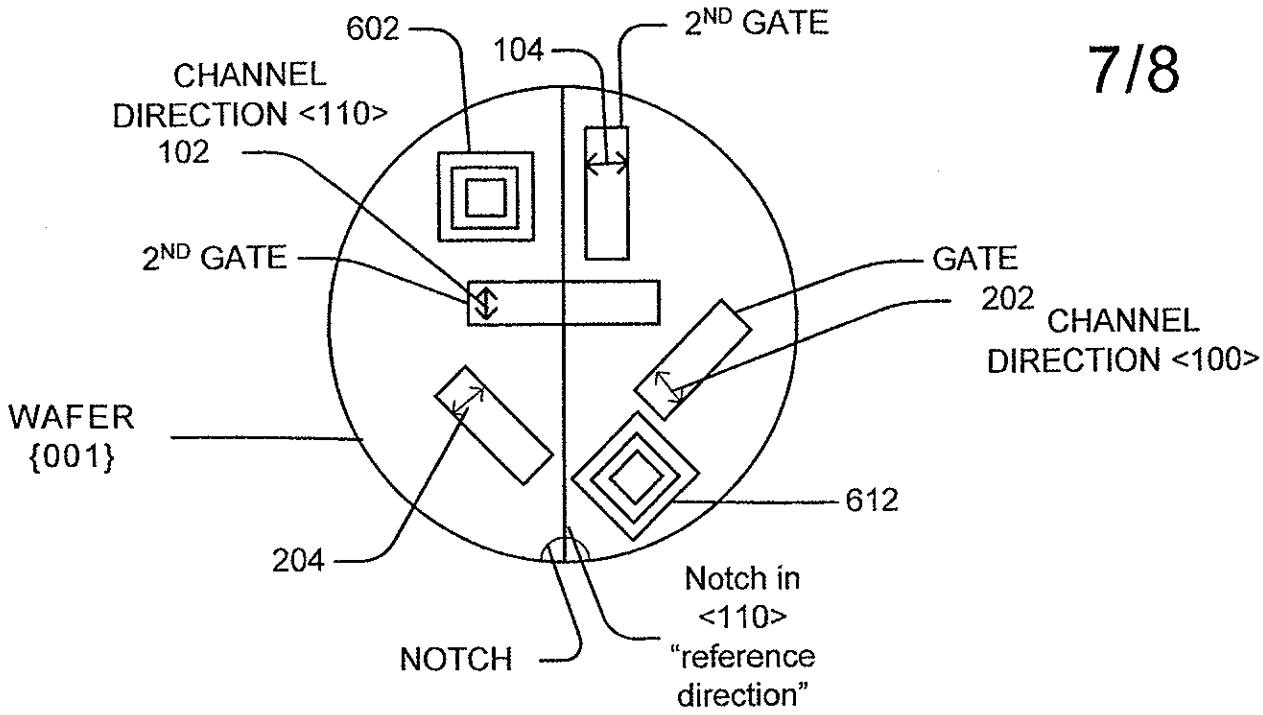
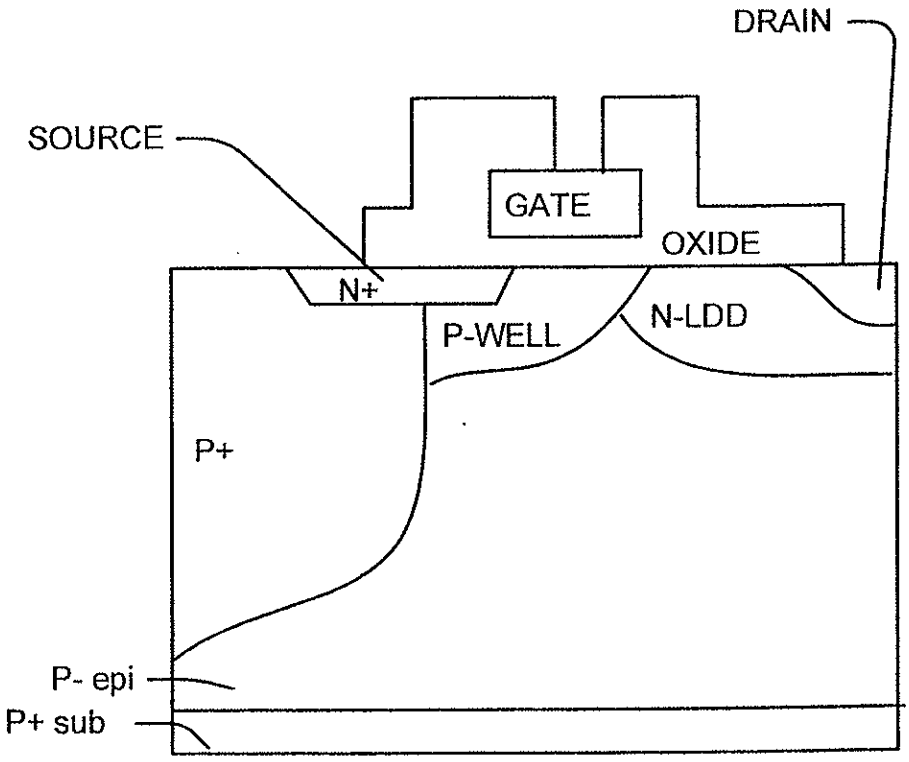
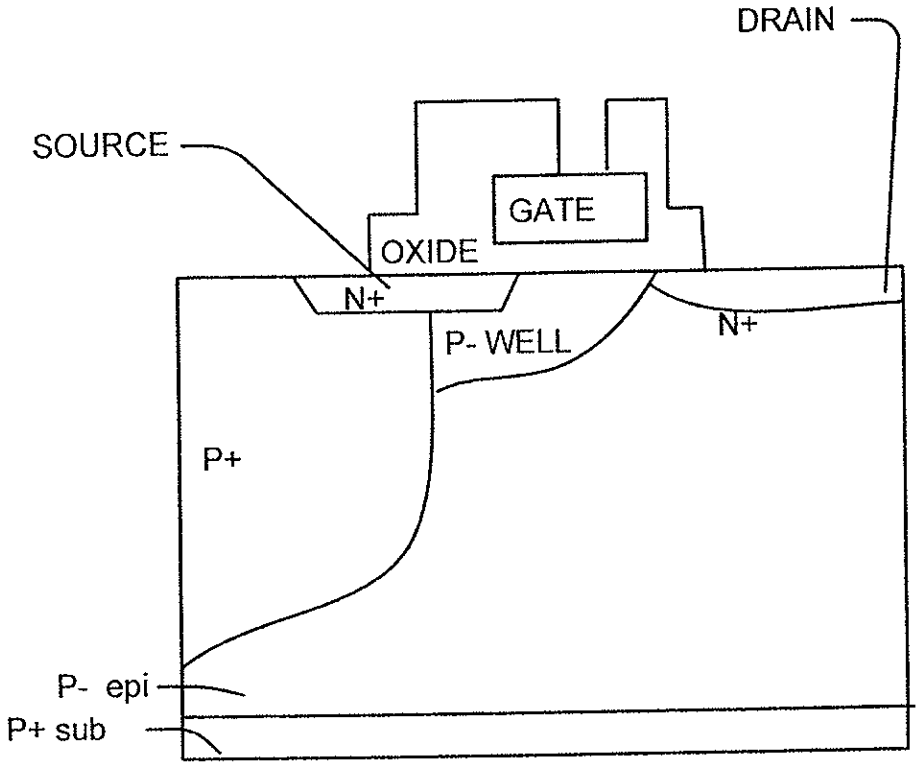


FIGURE 6



OFFSET LDMOS

FIGURE 7



NON-OFFSET LDMOS

FIGURE 8